

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-114952

(43)Date of publication of application : 21.04.2000

(51)Int.Cl.

H03K 19/00  
H03K 19/0948

(21)Application number : 11-314744

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(22)Date of filing : 25.12.1992

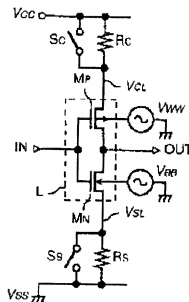
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(30)Priority

Priority number : 04094077 Priority date : 14.04.1992 Priority country : JP

## (54) SEMICONDUCTOR INTEGRATED CIRCUIT

(57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor integrated circuit high in operating speed and low in power consumption.**SOLUTION:** Means (switches  $S_c$  and  $S_s$  and resistance  $R_c$  and  $R_s$ ) for controlling the current supply of large and small currents are inserted between an MOS transistor circuit (L) and power sources ( $V_{cc}$  and  $V_{ss}$ ), to make substrate potential variable. Thus, it is possible to select a small current and obtain a low power consumption property when it is in a standby state and to select a large current and obtain rapidly when it operates.

## LEGAL STATUS

[Date of request for examination] 05.11.1999

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]	3436209
[Date of registration]	06.06.2003
[Number of appeal against examiner's decision of rejection]	
[Date of requesting appeal against examiner's decision of rejection]	
[Date of extinction of right]	